

# MMBTA92L, SMMBTA92L, MMBTA93L

## High Voltage Transistors

### PNP Silicon

#### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	92	93	Unit
Collector–Emitter Voltage	$V_{CEO}$	-300	-200	Vdc
Collector–Base Voltage	$V_{CBO}$	-300	-200	Vdc
Emitter–Base Voltage	$V_{EBO}$	-5.0	-5.0	Vdc
Collector Current — Continuous	$I_C$	-500		mAdc

#### DEVICE MARKING

MMBTA92L, SMMBTA92L = 2D; MMBTA93LT1 = 2E

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	225	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation (Note 2) Alumina Substrate, $(2) T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300	mW
		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

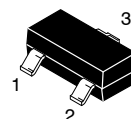
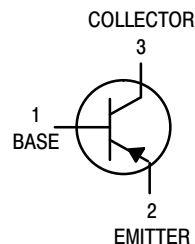
1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



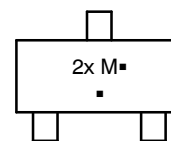
ON Semiconductor®

<http://onsemi.com>



SOT-23 (TO-236AF)  
CASE 318  
STYLE 6

#### MARKING DIAGRAM



2x = Specific Device Code  
M = Date Code\*  
▪ = Pb-Free Package

(\*Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBTA92LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
SMMBTA92LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBTA92LT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
SMMBTA92LT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
MMBTA93LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Breakdown Voltage (Note 3) ( $I_C = -1.0\text{ mA}$ , $I_B = 0$ )	$V_{(BR)CEO}$	-300 -200	-	Vdc
Collector–Base Breakdown Voltage ( $I_C = -100\text{ }\mu\text{A}$ , $I_E = 0$ )	$V_{(BR)CBO}$	-300 -200	-	Vdc
Emitter–Base Breakdown Voltage ( $I_E = -100\text{ }\mu\text{A}$ , $I_C = 0$ )	$V_{(BR)EBO}$	-5.0	-	Vdc
Collector Cutoff Current ( $V_{CB} = -200\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = -160\text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	-	-0.25 -0.25	$\mu\text{A}$
Emitter Cutoff Current ( $V_{EB} = -3.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	-	-0.1	$\mu\text{A}$

## ON CHARACTERISTICS (Note 3)

DC Current Gain ( $I_C = -1.0\text{ mA}$ , $V_{CE} = -10\text{ Vdc}$ ) ( $I_C = -10\text{ mA}$ , $V_{CE} = -10\text{ Vdc}$ )  ( $I_C = -30\text{ mA}$ , $V_{CE} = -10\text{ Vdc}$ )	Both Types Both Types MMBTA92, SMMBTA92 MMBTA93	$h_{FE}$	25 40 25 25	- - - -	-
Collector–Emitter Saturation Voltage ( $I_C = -20\text{ mA}$ , $I_B = -2.0\text{ mA}$ )	MMBTA92, SMMBTA92 MMBTA93	$V_{CE(sat)}$	- -	-0.5 -0.5	Vdc
Base–Emitter Saturation Voltage ( $I_C = -20\text{ mA}$ , $I_B = -2.0\text{ mA}$ )		$V_{BE(sat)}$	-	-0.9	Vdc

## SMALL-SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ( $I_C = -10\text{ mA}$ , $V_{CE} = -20\text{ Vdc}$ , $f = 100\text{ MHz}$ )		$f_T$	50	-	MHz
Collector–Base Capacitance ( $V_{CB} = -20\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	MMBTA92, SMMBTA92 MMBTA93	$C_{cb}$	- -	6.0 8.0	pF

3. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

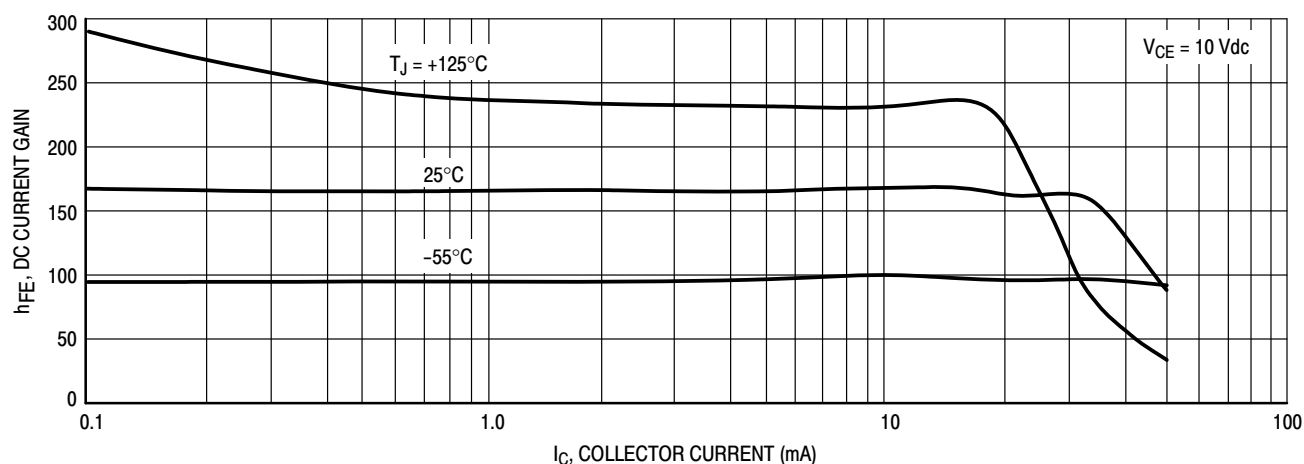


Figure 1. DC Current Gain

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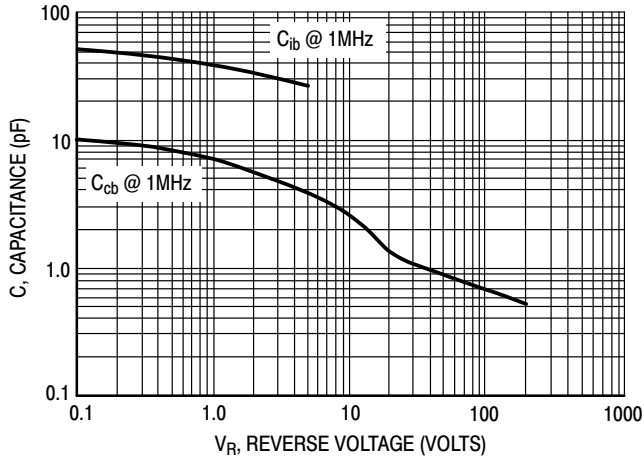


Figure 2. Capacitance

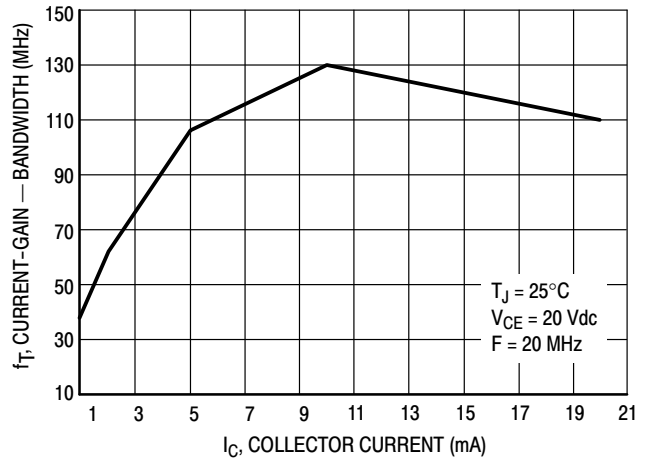


Figure 3. Current-Gain - Bandwidth

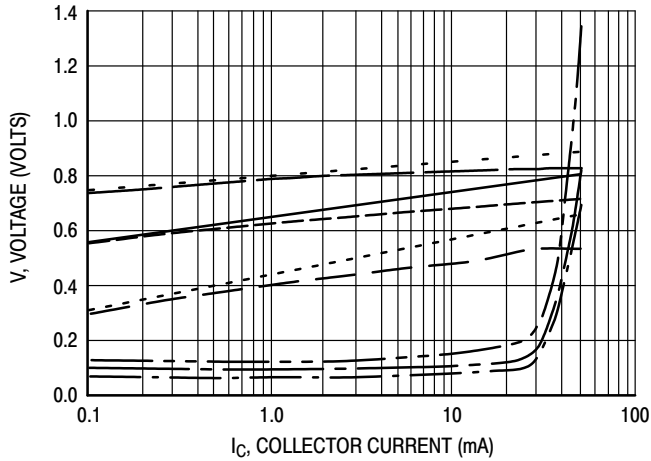


Figure 4. "ON" Voltages

- $V_{CE(sat)}$  @  $25^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{CE(sat)}$  @  $125^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{CE(sat)}$  @  $-55^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @  $25^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @  $125^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(sat)}$  @  $-55^\circ\text{C}$ ,  $I_C/I_B = 10$
- $V_{BE(on)}$  @  $25^\circ\text{C}$ ,  $V_{CE} = 10\text{ V}$
- $V_{BE(on)}$  @  $125^\circ\text{C}$ ,  $V_{CE} = 10\text{ V}$
- $V_{BE(on)}$  @  $-55^\circ\text{C}$ ,  $V_{CE} = 10\text{ V}$

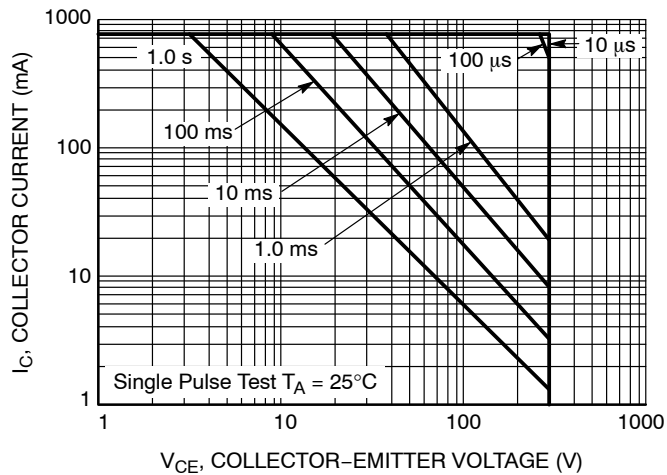
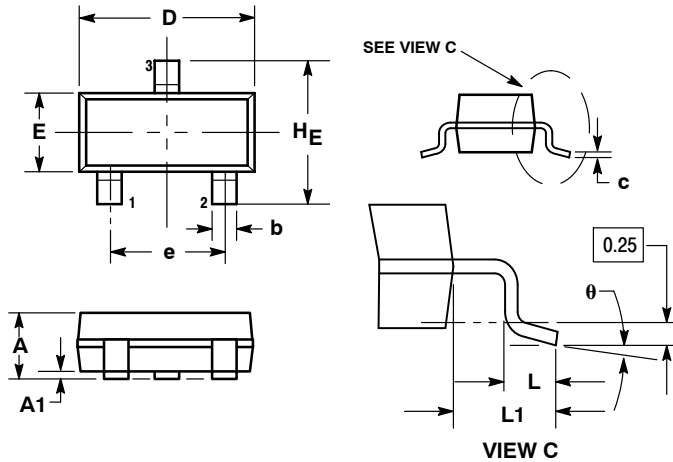


Figure 5. Safe Operating Area

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## PACKAGE DIMENSIONS

SOT-23 (TO-236)  
CASE 318-08  
ISSUE AP



NOTES:

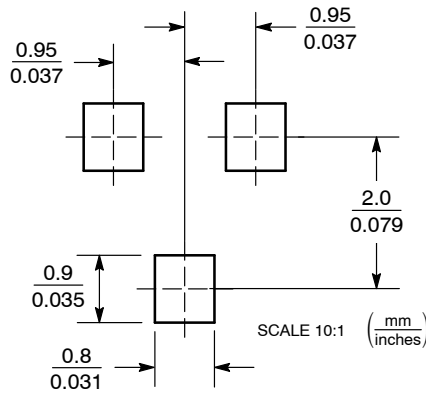
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

### SOLDERING FOOTPRINT



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